

Vishay Semiconductors

HEXFRED®, Ultrafast Soft Recovery Diode, 15 A



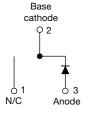


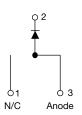
TO-263AB (D²PAK)

TO-262AA



VS-HFA15 TB60-1PbF

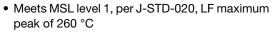




PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK), TO-262AA							
I _{F(AV)}	15 A							
V _R	600 V							
V _F at I _F	1.2 V							
t _{rr} (typ.)	23 ns							
T _J max.	150 °C							
Diode variation	Single die							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}





· Designed and qualified for industrial level

RoHS COMPLIANT

• AEC-Q101 qualified

HALOGEN FREE

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- · Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V_R		600	V					
Maximum continuous forward current	I _F	T _C = 100 °C	15						
Single pulse forward current	I _{FSM}		150	Α					
Maximum repetitive forward current	I _{FRM}		60						
Maximum navvey discination	P _D	T _C = 25 °C	74	W					
Maximum power dissipation		T _C = 100 °C	29	VV					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					



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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
Maximum forward voltage		I _F = 15 A		-	1.3	1.7	V
	V_{FM}	I _F = 30 A	See fig. 1	-	1.5	2.0	
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6	
Maximum reverse	1	V _R = V _R rated	See fig. 2	-	1.0	10	
leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	See lig. 2	-	400	1000	μA
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	25	50	pF
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CON	IDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time See fig. 5	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	_F = 1.0 A, dI _F /dt = 200 A/μs, V _R = 30 V		23	-		
	t _{rr1}	T _J = 25 °C		-	50	60	ns	
	t _{rr2}	T _J = 125 °C	I _F = 15 A dI _F /dt = 200 A/μs V _R = 200 V	-	105	120		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	6.0	A nC	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	6.5	10		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	84	180		
See fig. 7	Q _{rr2}	T _J = 125 °C		-	241	600	iiC	
Peak rate of fall of recovery current during the	dI _{(rec)M} /dt1	T _J = 25 °C		-	188	-	A/µs	
See fig. 8	dI _{(rec)M} /dt2	T _J = 125 °C		-	160	-	ΑνμS	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	1.7			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-			
Weight			-	2.0	-	g		
vveignit			-	0.07	-	oz.		
Marking daviso		Case style D ² PAK		HFA15	TB60S			
Marking device		Case style TO-262	HFA15TB60-1					





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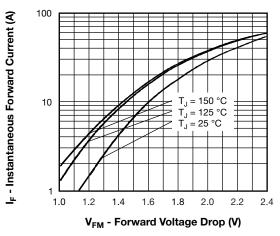


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

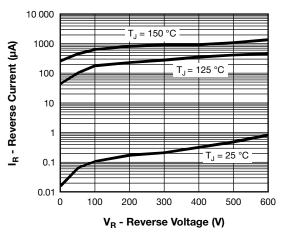


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

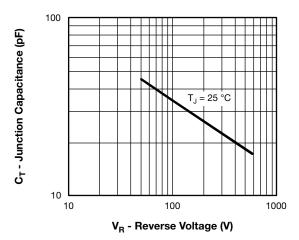


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

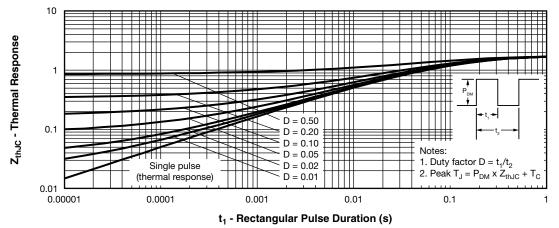


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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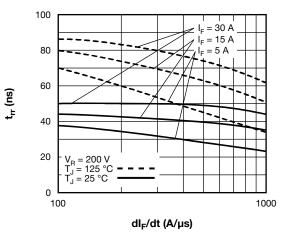


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

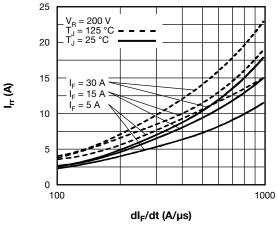


Fig. 6 - Typical Recovery Current vs. dl_F/dt

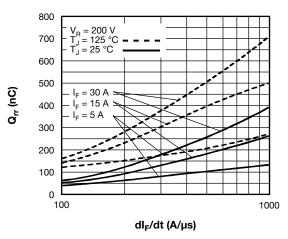


Fig. 7 - Typical Stored Charge vs. dl_F/dt

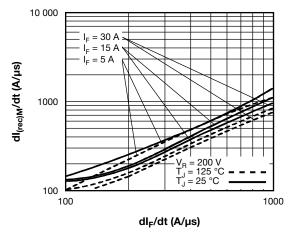


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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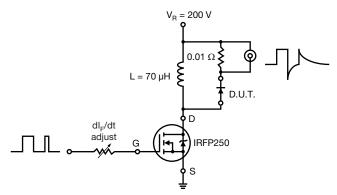
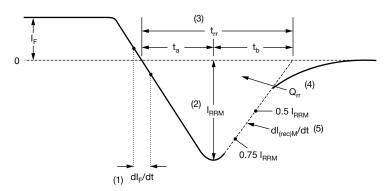


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \boldsymbol{Q}_{rr} area under curve defined by \boldsymbol{t}_{rr} and \boldsymbol{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

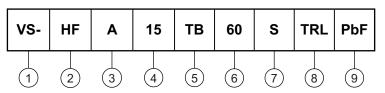
(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

Current rating (15 = 15 A)

5 - Package:

TB = TO-220

Voltage rating (60 = 600 V)

- • S = D²PAK

- • -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D2PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

9 - PbF = lead (Pb)-free

- P = lead (Pb)-free (for D²PAK TRL and TRR)

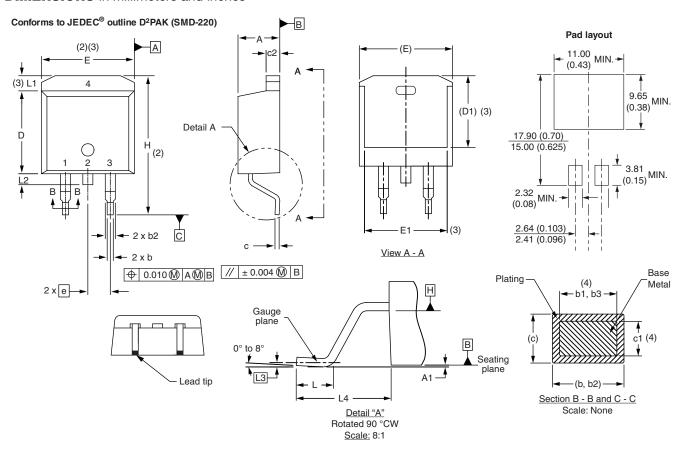
LINKS TO RELATED DOCUMENTS						
Dimensions	TO-263AB (D ² PAK): www.vishay.com/doc?95046					
Differsions	TO-262AA: www.vishay.com/doc?95419					
Part marking information	TO-263AB (D ² PAK): www.vishay.com/doc?95054					
Fart marking information	TO-262AA: www.vishay.com/doc?95420					
Packaging information	www.vishay.com/doc?95032					
SPICE model	www.vishay.com/doc?95357					



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS INCHES		NOTES	S SYMBOL	MILLIMETERS		INCHES		NOTES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	31MBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB

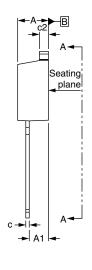


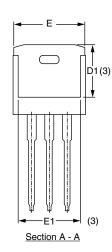
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TO-262

DIMENSIONS in millimeters and inches

Modified JEDEC outline TO-262 (Datum A)—(2) (3) E A (3) L1 D L2 B B B L (2) 3 x b2 3 x b2



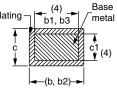


⊕ 0.010**⋒**|A**⋒**|B

Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode
3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIN	METERS	INCH	INCHES		
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100	BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

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